

Taiwan Semiconductor

1A, 20 - 40V Schottky Barrier Surface Mount Rectifier

FEATURES

- Plastic package has carries underwriters
- Ideal for automated placement
- Surge overload rating to 25A peak
- Reliable low cost construction utilizing molded
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Inverters
- Converters
- Adapters

MECHANICAL DATA

- Case: MELF
- Meet JESD 201 class 1A whisker test
- Polarity: Indicated by cathode band
- Weight: 120.00mg (approximately)

KEY PARAMETERS			
PARAMETER VALUE UNIT			
I _F	1	A	
V _{RRM}	20 - 40	V	
I _{FSM}	25	А	
T _{J MAX}	125	°C	
Package	MELF		
Configuration	Single die		





Μ	EI	LF



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)					
PARAMETER	SYMBOL	LL5817	LL5818	LL5819	UNIT
Repetitive peak reverse voltage	V _{RRM}	20	30	40	V
Reverse voltage, total rms value	V _{R(RMS)}	14	21	28	V
DC blocking voltage	V _{DC}	20	30	40	V
Forward current	I _F	1		А	
Surge peak forward current 8.3ms single half sine-wave superimposed on rated load	I _{FSM}	25			А
Junction temperature	TJ	-65 to +125		°C	
Storage temperature	T _{STG}	-65 to +125			°C



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-Ambient thermal resistance	R _{eja}	80	°C/W

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)

PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	LL5817	$I_F = 1A$		-	0.450	V
		I _F = 3A	V _F	-	0.750	V
-	LL5818	$I_F = 1A$		-	0.550	V
		I _F = 3A		-	0.875	V
	LL5819	$I_F = 1A$		-	0.600	V
		I _F = 3A		-	0.900	V
Reverse current @ rated V _R ⁽²⁾		$T_J = 25^{\circ}C$	I _R	-	0.5	mA
		T _J = 100°C		-	5	mA
Junction capacitance		1MHz, $V_{R} = 4.0V$	CJ	110	-	pF

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION

ORDERING CODE ⁽¹⁾	PACKAGE	PACKING
LL581x L0G	MELF	5,000/13" reel

Notes:

1. "x" defines voltage from 20V(LL5817) to 40V(LL5819)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve



Fig.3 Typical Forward Characteristics



Fig.5 Typical Junction Capacitance



Fig.2 Maximum Non-Repetitive Peak Forward Surge Current



Number of Cycles at $60H_Z$

Fig.4 Typical Reverse Characteristics



Fig.6 Typical Transient Thermal Impedance





PACKAGE OUTLINE DIMENSIONS

MELF



	Unit (mm)		Unit (inch)		
DIM	Min	Max	Min	Max	
А	4.80	5.50	0.189	0.217	
В	2.25	2.67	0.089	0.105	
С	0.30	0.60	0.012	0.024	

SUGGESTED PAD LAYOUT



DIM	Unit (mm)	Unit (inch)
DIIVI	ТҮР	ТҮР
С	4.80	0.189
G	3.30	0.130
Х	1.50	0.059
X1	6.30	0.248
Y	2.70	0.106



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